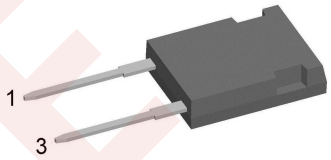
FRED

V_{RRM} = 1000 V
I_{FAV} = 30 A
t_{rr} = 45 ns

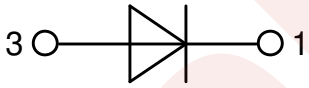
Fast Recovery Epitaxial Diode
Single Diode

Part number

DSEI30-10AR



Backside: isolated



Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: ISOPLUS247

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

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Fast Diode

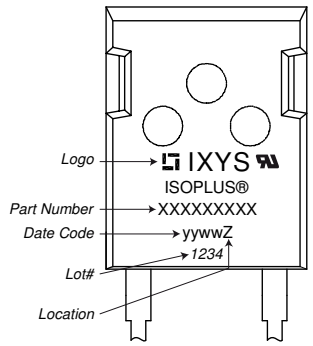
Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1000	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1000	V
I_R	*reverse current, drain current*	V_R = 1000 V	T_{VJ} = 25°C			750	µA
		V_R = 800 V	T_{VJ} = 125°C			7	mA
V_F	*forward voltage drop*	I_F = 30 A	T_{VJ} = 25°C			2.36	V
		I_F = 60 A				2.67	V
		I_F = 30 A	T_{VJ} = 150°C			2.00	V
		I_F = 60 A				2.50	V
I_{FAV}	*average forward current*	T_C = 70°C	T_{VJ} = 150°C			30	A
		rectangular d = 0.5					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			1.53	V
r_F	*slope resistance* }					15.5	mΩ
R_{thJC}	*thermal resistance junction to case*					1.1	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.25		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			115	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine; V_R = 0 V	T_{VJ} = 45°C			200	A
C_J	*junction capacitance*	V_R = 600 V f = 1 MHz	T_{VJ} = 25°C		16		pF
I_{RM}	*max. reverse recovery current*		T_{VJ} = 25°C		9		A
		I_F = 30 A; V_R = 540 V	T_{VJ} = 100°C		13		A
t_{rr}	*reverse recovery time*	$-di_F/dt$ = 200 A/µs	T_{VJ} = 25°C		90		ns
			T_{VJ} = 100°C		150		ns

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Package ISOPLUS247				Ratings			
Symbol	**Definition**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal				70	A
T_{VJ}	*virtual junction temperature*			-40		150	°C
T_{op}	*operation temperature*			-40		125	°C
T_{stg}	*storage temperature*			-40		150	°C
Weight					6		g
F_C	*mounting force with clip*			20		120	N
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	5.4			mm
$d_{Spb/Apb}$			*terminal to backside*	4.1			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA	3600			V
		t = 1 minute		3000			V

Product Marking

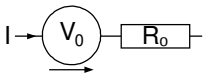


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI30-10AR	DSEI30-10AR	Tube	30	481947

Similar Part	Package	Voltage class
DSEI30-10A	TO-247AD (2)	1000
DSEI30-12A	TO-247AD (2)	1200

Equivalent Circuits for Simulation

** on die level* T_{VJ} = 150°C

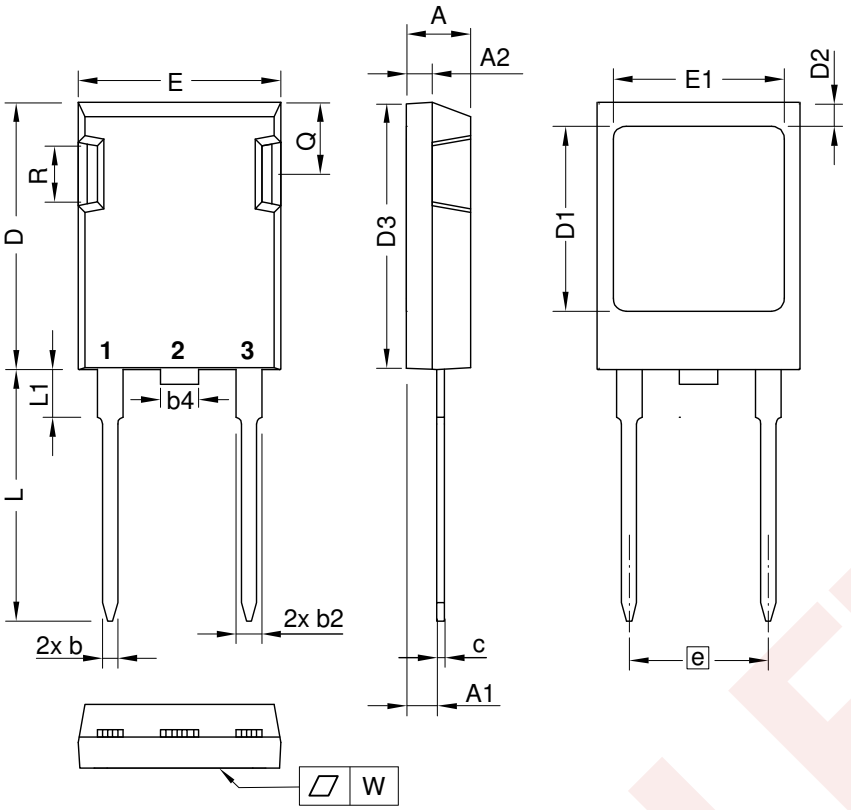


		Fast Diode	
$V_{0\,max}$	*threshold voltage*	1.53	V
$R_{0\,max}$	*slope resistance **	13	mΩ

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Outlines ISOPLUS247

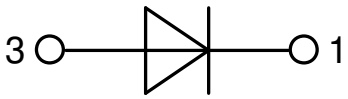


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.085
b	1.14	1.40	0.045	0.055
b2	1.91	2.20	0.075	0.087
b4	2.92	3.24	0.115	0.128
c	0.61	0.83	0.024	0.033
D	20.80	21.34	0.819	0.840
D1	15.75	16.26	0.620	0.640
D2	1.65	2.15	0.065	0.085
D3	20.30	20.70	0.799	0.815
E	15.75	16.13	0.620	0.635
E1	13.21	13.72	0.520	0.540
e	10.90 BSC		0.429 BSC	
L	19.81	20.60	0.780	0.811
L1	3.81	4.38	0.150	0.172
Q	5.59	6.20	0.220	0.244
R	4.25	5.50	0.167	0.217
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite
The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-247 AD gemäß JEDEC außer Schraubloch und L_{max}.
This drawing will meet all dimensions requiarement of JEDEC outline TO-247 AD except screw hole and except L_{max}.

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Fast Diode

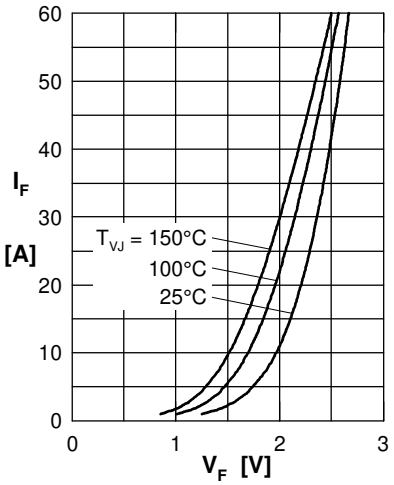


Fig. 1 Forward current I_F versus max. forward voltage drop V_F

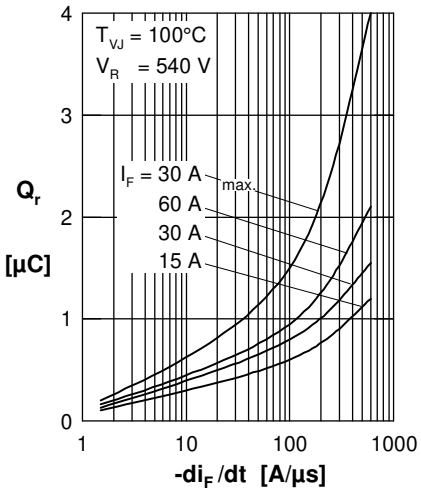


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

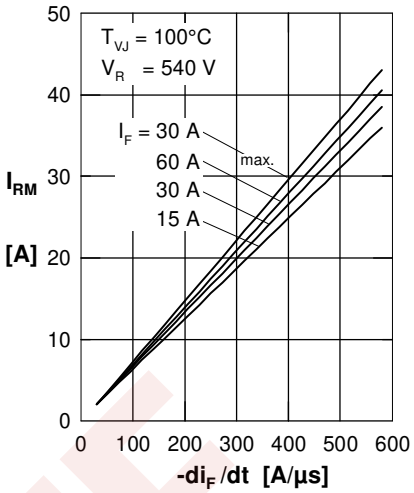


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

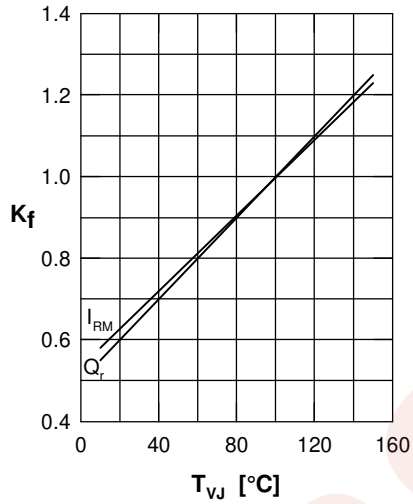


Fig. 4 Dynamic parameters Q_r, I_{RM} versus T_{VJ}

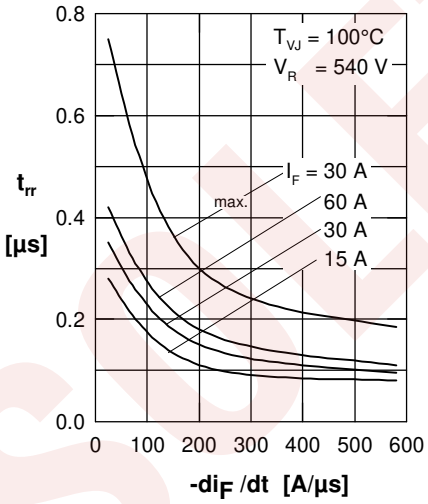


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

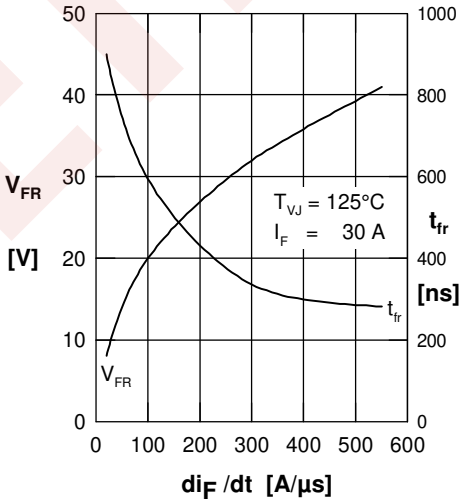


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

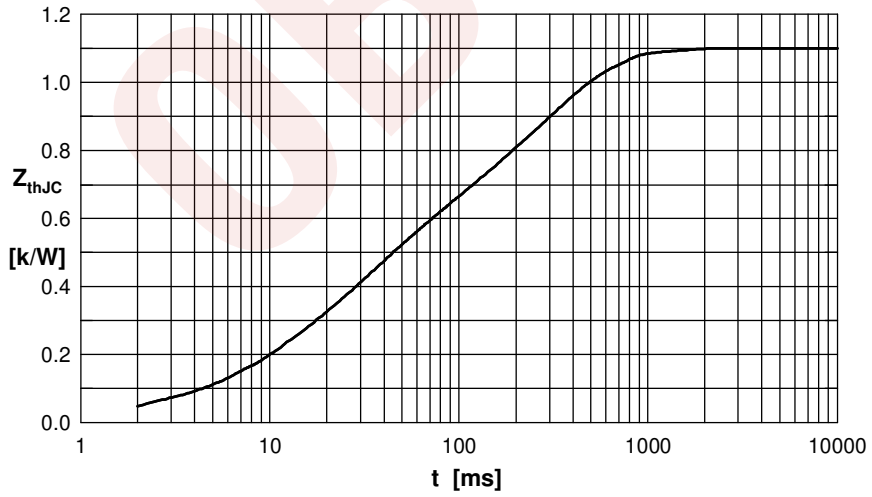


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.030	0.0100
2	0.100	0.0120
3	0.360	0.0300
4	0.610	0.2700

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